



N 沟道增强型场效应晶体管
N- CHANNEL MOSFET

JCS4AN120A

主要参数 MAIN CHARACTERISTICS

ID	4A
VDSS	1200 V
R _{dson} -max (@V _{gs} =10V)	4.0 Ω
Q _{g-typ}	39nC

用途

- 高频开关电源
- 电子镇流器
- UPS 电源

APPLICATIONS

- High efficiency switch mode power supplies
- Electronic lamp ballasts based on half bridge
- UPS

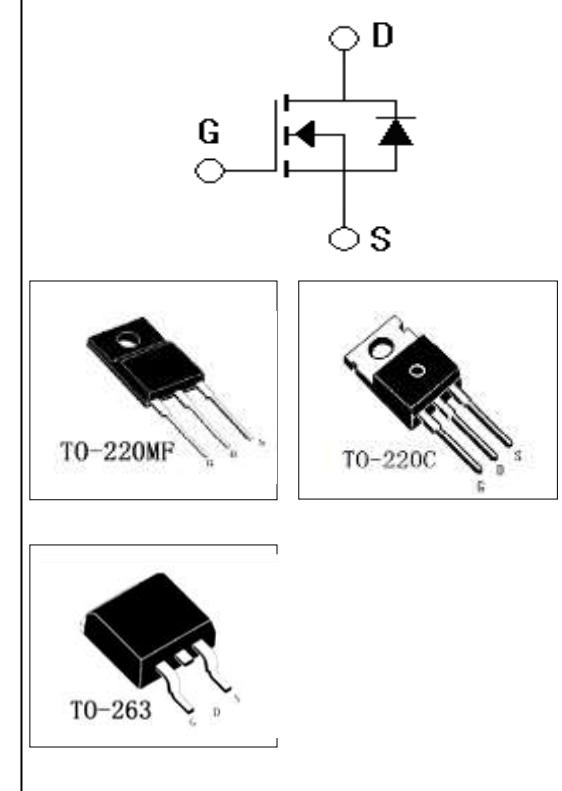
产品特性

- 低栅极电荷
- 低 C_{rss} (典型值 98pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

FEATURES

- Low gate charge
- Low C_{rss} (typical 98pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JCS4AN120FA-F-B	JCS4AN120FA-F-BR	N/A	N/A	JCS4AN120FA	TO-220MF
JCS4AN120CA-C-B	JCS4AN120CA-C-BR	N/A	N/A	JCS4AN120CA	TO-220C
N/A	JCS4AN120SA-S-BR	N/A	JCS4AN120SA-S-AR	JCS4AN120SA	TO-263



吉林华微电子股份有限公司
JILIN SINO-MICROELECTRONICS CO.,LTD.



JCS4AN120A

绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^\circ\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value		单 位 Unit
		JCS4AN120FA	JCS4AN120SA/CA	
最高漏极—源极直流电压 Drain-Source Voltage	V_{DSS}	1200		V
连续漏极电流 Drain Current -continuous	$I_D \quad T=25^\circ\text{C}$ $T=100^\circ\text{C}$	4*		A
		2.4*		A
最大脉冲漏极电流 (注 1) Drain Current -pulse (note 1)	I_{DM}	16*		A
最高栅源电压 Gate-Source Voltage	V_{GS}	± 30		V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E_{AS}	83		mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I_{AR}	4		A
重复雪崩能量 (注1) Repetitive Avalanche Current (note 1)	E_{AR}	11		mJ
二极管反向恢复最大电压变化速率 (注3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5		V/ns
耗散功率 Power Dissipation	$P_D \quad T_c=25^\circ\text{C}$ -Derate above 25°C	48	286	W
		0.4	2.3	
最高结温及存储温度 Operating and Storage Temperature Range	$T_J, \quad T_{STG}$	-55~+150		°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300		°C

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature



JCS4AN120A

电特性 ELECTRICAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最 小 Min	典 型 Typ	最 大 Max	单 位 Units
关态特性 Off -Characteristics						
漏一源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	1200	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_J$	$I_D=250\mu A$, referenced to 25°C	-	0.5	-	V/°C
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=1200V, V_{GS}=0V, T_c=25^{\circ}C$	-	-	10	μA
		$V_{DS}=1200V, T_c=125^{\circ}C$	-	-	300	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	3.0	-	5.0	V
正向跨导 Forward Transconductance	g_{fs}	$V_{DS} = 30V, I_D=2$ (note 4)	-	4.2	-	S
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=2A$	-	2.9	4	Ω
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{iss}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	833	1250	pF
输出电容 Output capacitance	C_{oss}		-	150	225	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	98	147	pF



电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
开关特性 Switching -Characteristics						
延迟时间 Turn-On delay time	$t_d(\text{on})$	V _{DD} =600V	-	29	43.5	ns
上升时间 Turn-On rise time	t_r	I _D =4A	-	55	82.5	ns
延迟时间 Turn-Off delay time	$t_d(\text{off})$	V _{GS} =10V	-	94	141	ns
下降时间 Turn-Off Fall time	t_f	R _G =25Ω	-	88	132	ns
栅极电荷总量 Total Gate Charge	Q _g	V _{DS} =960V ,	-	39	58.5	nC
栅一源电荷 Gate-Source charge	Q _{gs}	I _D =4A	-	6	9	nC
栅一漏电荷 Gate-Drain charge	Q _{gd}	V _{GS} =10V (note 4, 5)	-	25	37.5	nC
漏一源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain-Source Diode Forward Current		I _S	-	-	4	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}	-	-	16	A
正向导通压降 Forward on voltage	V _{SD}	V _{GS} =0V, I _S =4A	-		1.6	V
反向恢复时间 Reverse recovery time	t_{rr}	V _{GS} =0V, I _S =4A,		595		ns
反向恢复电荷 Reverse recovery charge	Q _{rr}	dI _F /dt=100A/μs (note 4)		4.9		μC

热特性 THERMAL CHARACTERISTIC

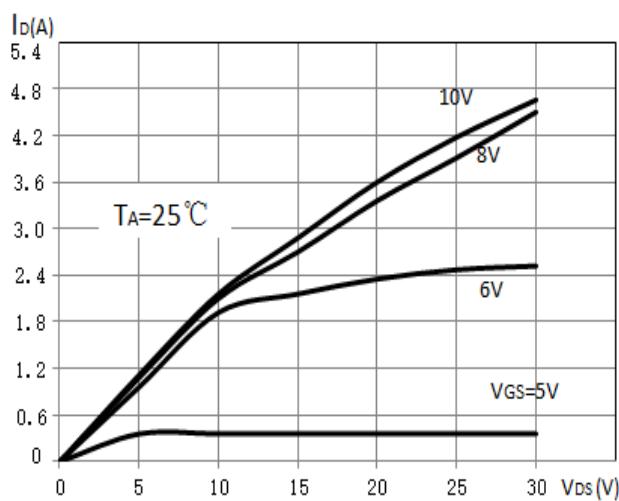
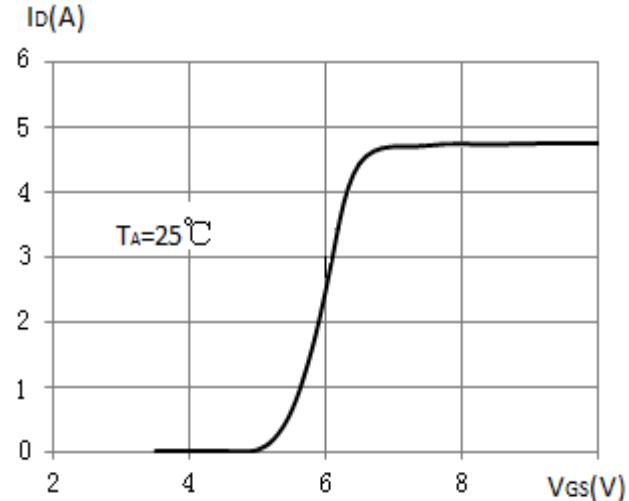
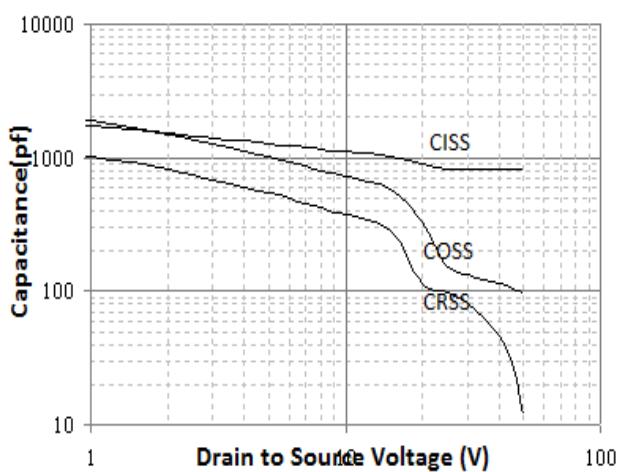
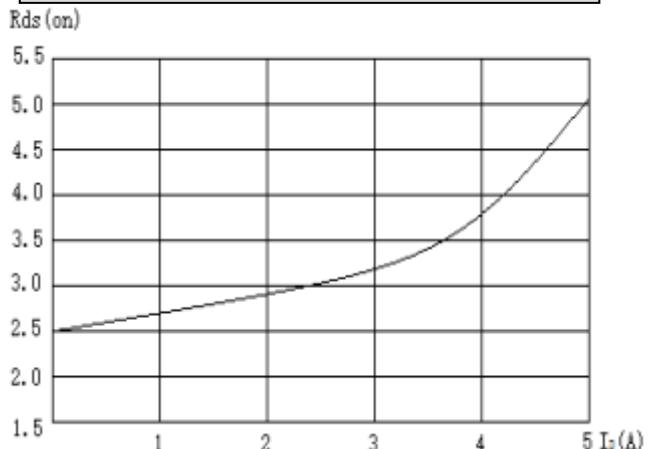
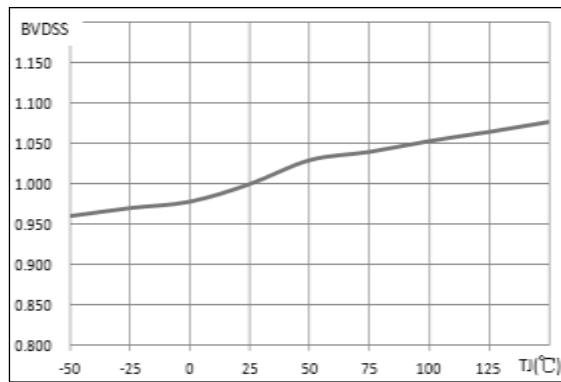
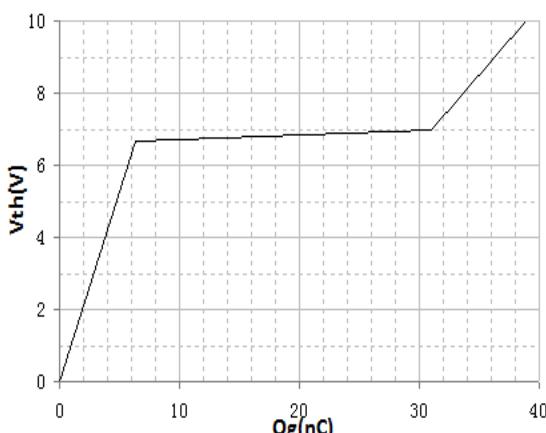
项目 Parameter	符号 Symbol	最大值 Value		单位 Unit
		JCS4AN120FA	JCS4AN120SA/CA	
结到管壳的热阻 Thermal Resistance, Junction to Case	R _{th(j-c)}	2.6	0.35	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	R _{th(j-A)}	62.5	40	°C/W

注:

- 1: 脉冲宽度由最高结温限制
 2: L=10mH,I_{AS}=4.0A, V_{DD}=50V, R_G=25Ω, 起始结温 T_J=25°C
 3: I_{SD} ≤ 4A, dI/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, 起始结温 T_J=25°C
 4: 脉冲测试: 脉冲宽度≤300μs, 占空比≤2%
 5: 基本与工作温度无关

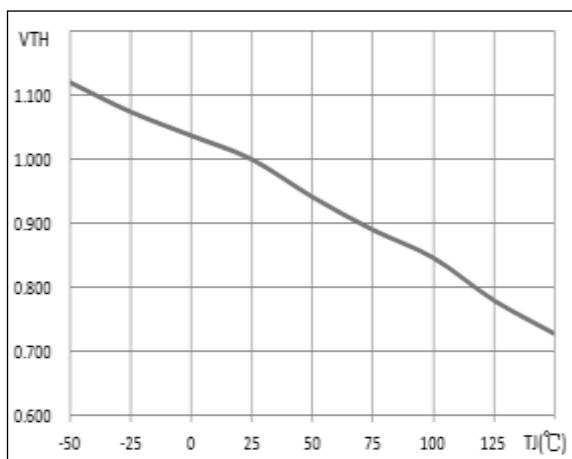
Notes:

- 1: Pulse width limited by maximum junction temperature
 2: L=10mH,I_{AS}=4.0A, V_{DD}=50V, R_G=25Ω, =25Ω, Starting T_J=25°C
 3: I_{SD} ≤ 4A, dI/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J=25°C
 4: Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%
 5: Essentially independent of operating temperature

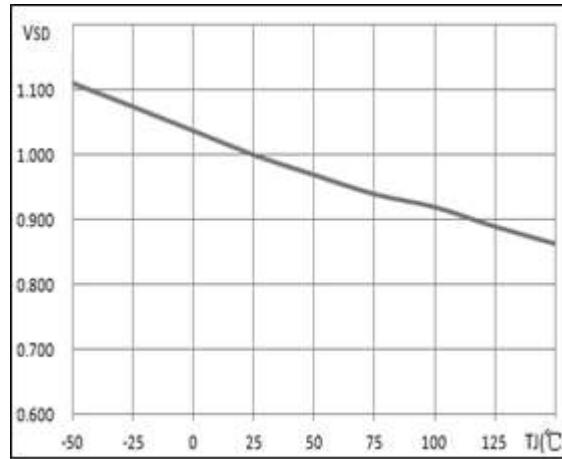
特征曲线 ELECTRICAL CHARACTERISTICS (curves)
Output characteristics

Transfer characteristics

Capacitance Characteristics

On-Resistance Variations. I_D

Normalized $BVDSS$ vs. temperature

Gate charge vs. V_{GS}

吉林华微电子股份有限公司
JILIN SINO-MICROELECTRONICS CO.,LTD

特征曲线 ELECTRICAL CHARACTERISTICS (curves)

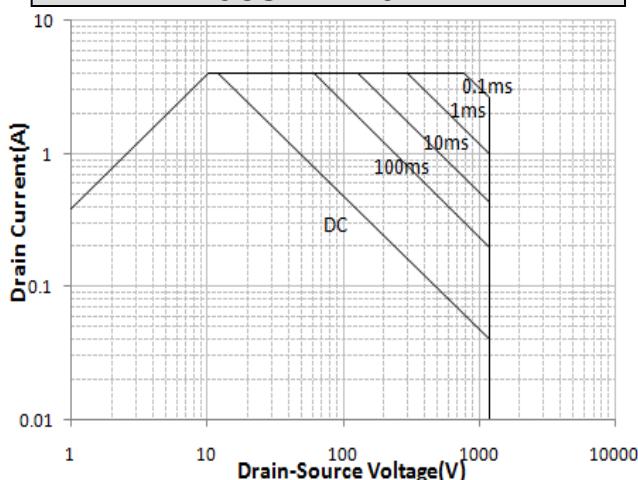
Normalized VTH vs. temperature



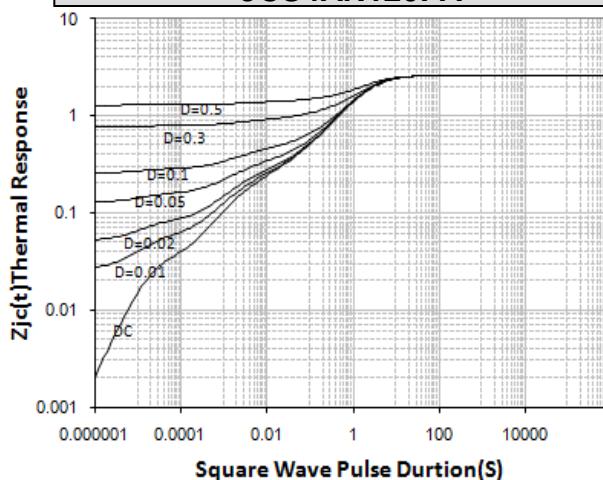
Normalized VSD vs. temperature



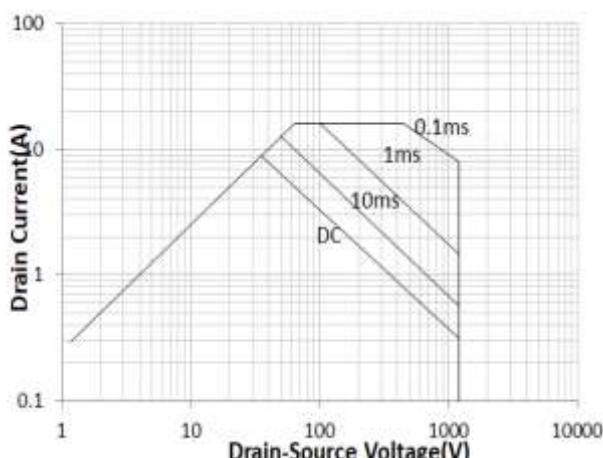
Maximum Safe Operating Area for JCS4AN120FA



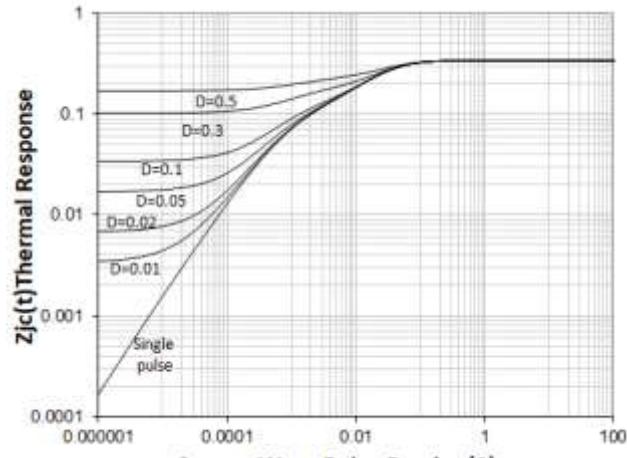
Thermal impedance for JCS4AN120FA



Maximum Safe Operating Area for JCS4AN120SA/CA



Thermal impedance for JCS4AN120SA/CA

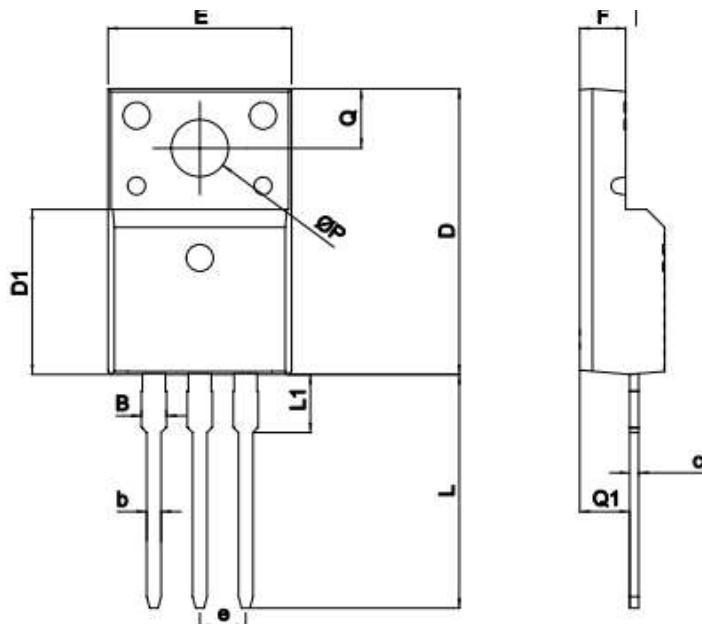
吉林华微电子股份有限公司
JILIN SINO-MICROELECTRONICS CO.,LTD



外形尺寸 PACKAGE MECHANICAL DATA

TO-220MF

单位 Unit: mm



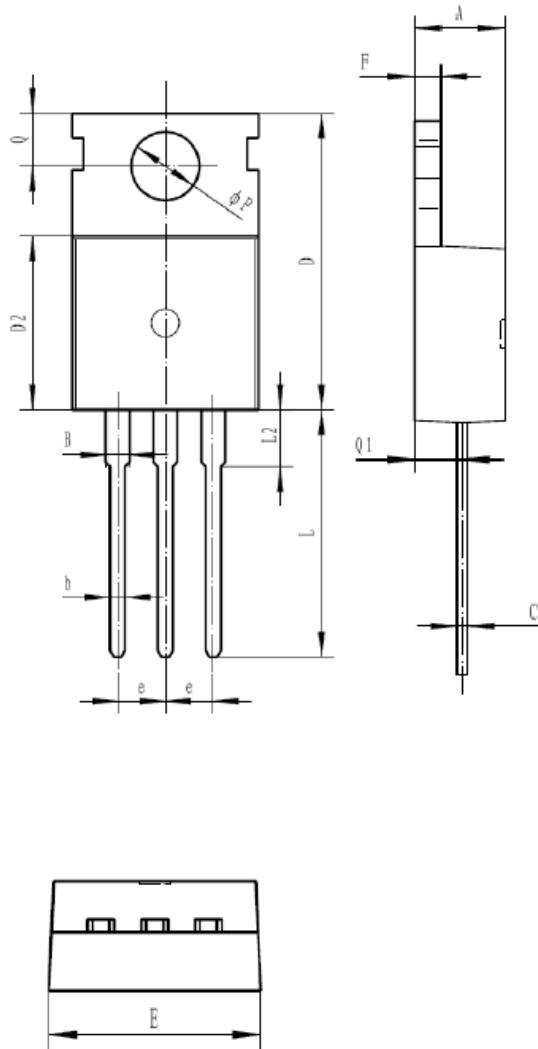
SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B	1.22	1.47
b	0.7	0.9
c	0.45	0.60
D	15.6	16.1
D1	9.0	9.3
e	2.54TYPE	
E	9.9	10.4
F	2.3	2.8
L	12.6	13.3
L1	3.1	3.4
Q	3.2	3.4
Q1	2.6	2.9
ΦP	3.0	3.5





外形尺寸 PACKAGE MECHANICAL DATA

TO-220C

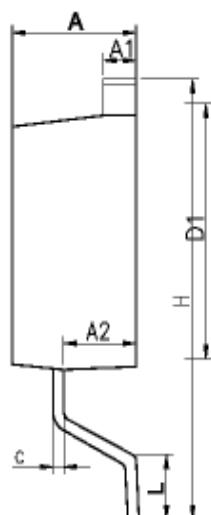
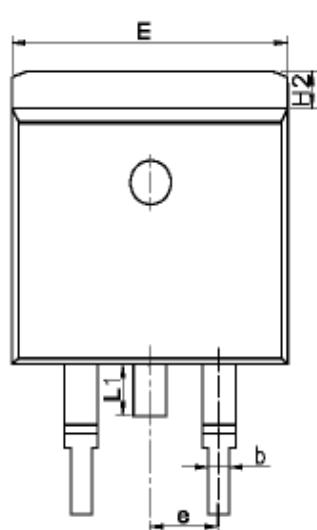


符号 symbol	MIN	MAX
A	4.30	4.70
B	1.22	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80



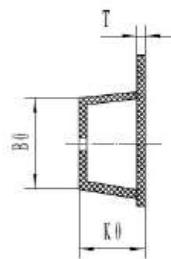
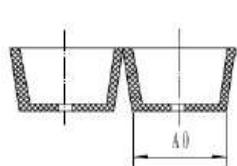
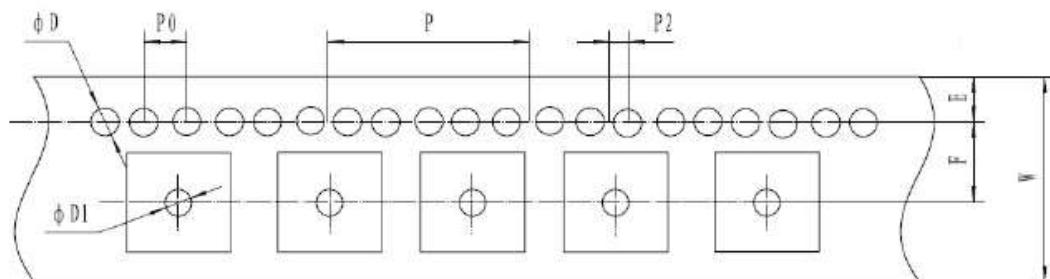
外形尺寸 PACKAGE MECHANICAL DATA

TO-263



SYMBOL	MM	
	MIN	MAX
A	4.30	4.80
A1	1.12	1.42
A2	2.54	2.84
b	0.67	1.00
c	0.29	0.52
D1	8.40	9.00
E	9.80	10.46
e	2.54 BSC	
H	14.00	16.00
H2	1.12	1.45
L	1.50	3.10
L1	1.45	1.70

编带 REEL



产品尺寸规格 (UNIT:mm)					
规格	Y	A0	E	P	D
尺寸	24 ± 0.3	10.9 ± 0.1	1.75 ± 0.1	11.5 ± 0.1	$1.5 \pm 0.1/-0$
规格	D1	P0	P2	P	T
尺寸	$1.5 \pm 0.1/-0$	4 ± 0.1	2 ± 0.1	16 ± 0.1	0.35 ± 0.05
规格	K0	B0			
尺寸	4.9 ± 0.1	16.6 ± 0.1			



注意事项

1. 吉林华微电子股份有限公司的产品销售分为直销和销售代理，无论哪种方式，订货时请与公司核实。
2. 购买时请认清公司商标，如有疑问请与公司本部联系。
3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知。

NOTE

1. Jilin Sino-microelectronics co., Ltd sales its product either through direct sales or sales agent , thus, for customers, when ordering , please check with our company.
2. We strongly recommend customers check carefully on the trademark when buying our product, if there is any question, please don't be hesitate to contact us.
3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
4. Jilin Sino-microelectronics co., Ltd reserves the right to make changes in this. specification sheet and is subject to change without prior notice.

联系方式

吉林华微电子股份有限公司

公司地址：吉林省吉林市深圳街 99 号

邮编：132013

总机：86-432-64678411

传真：86-432-64665812

网址：www.hwdz.com.cn

CONTACT

JILIN SINO-MICROELECTRONICS CO., LTD.

ADD: No.99 Shenzhen Street, Jilin City, Jilin Province, China.

Post Code: 132013

Tel: 86-432-64678411

Fax: 86-432-64665812

Web Site: www.hwdz.com.cn